

RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ✧ 0.8 INCHES (20.40MM) DIGIT HEIGHT
- ✧ 20.0MM×27.70MM OUTLINE
- ✧ SINGLE DIGIT
- ✧ SINGLE COLOR
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

DESCRIPTION

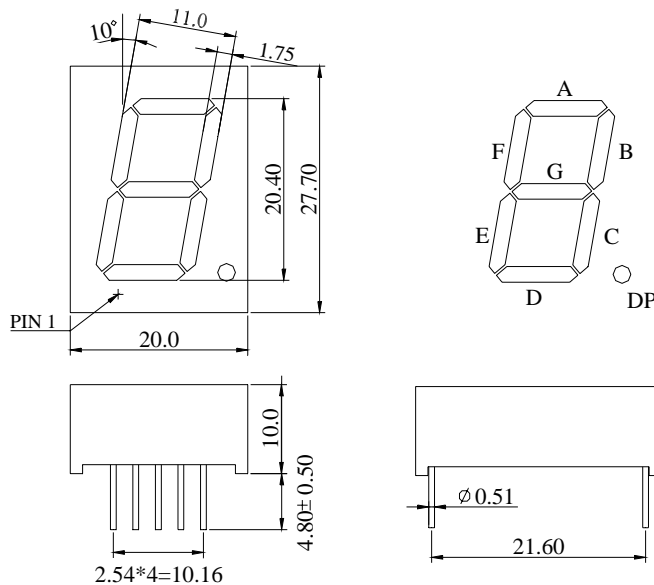
The REC-S8106CSR is a 0.8 inches (20.40mm) digit height, 20.0mm×27.70mm outline, single color, single digit with common cathode numeric display. This display utilizes super-red LED chips fabricated from GaAlAs epiwafer on GaAs substrate grown by liquid phase epitaxy. These devices have black face and white segments.

DEVICE

PART NO.	EMITTING COLOR	DESCRIPTION
REC-S8106CSR	Super-Red	Black Surface & White Segments

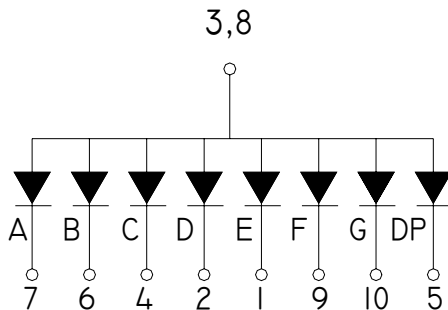
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PACKAGE DIMENSION



- Notes: 1. All dimension are in millimeters.
 2. Tolerance is ± 0.25 mm unless otherwise specified.

INTERNAL CIRCUIT DIAGRAM



PIN CONNECTION

PIN NO.	CONNECTION	PIN NO.	CONNECTION
1	Anode E	6	Anode B
2	Anode D	7	Anode A
3	Common Cathode	8	Common Cathode
4	Anode C	9	Anode F
5	Anode DP	10	Anode G

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PARAMETER	SYMBOL	MAXIMUM	UNIT
Power Dissipation per Seg.	P_{AD}	60	mW
Peak Forward Current per Seg. (1/10 Duty Cycle, 0.1ms Pules Width)	I_{PF}	60	mA
Continuous Forward Current per Seg.	I_{AF}	15	mA
Reverse Voltage per Seg.	V_R	20	V
Operating Temperature Range, T_{opr}	- 25° C to + 85° C		
Storage Temperature Range, T_{stg}	- 30° C to + 90° C		
Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C			

ELECTRO - OPTICAL CHARACTERISTICS AT $T_A=25^\circ\text{C}$

PARAMETER	UNIT	MIN	TYPE	MAX
Luminous Intensity per Chip., I_V ($I_F=20\text{mA}$)	mcd	7	10	12
Peak Emission Wavelength, λ_P ($I_F=20\text{mA}$)	nm		640	
Special Line Half-Width, $\Delta\lambda$ ($I_F=20\text{mA}$)	nm		20	
Forward Voltage per Seg., V_F ($I_F=20\text{mA}$)	V	1.6	1.8	2.2
Reverse Current per Seg., I_R , ($V_R=5\text{V}$)	μA			100
Luminous Intensity Matching Ratio, I_{V-m} ($I_F=20\text{mA}$)				2:1